



Attorney Docket No. 5347-208

PATENT

11/12/02
JMBR
Robert
Amat

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re:
Serial No.:
Filed:
For:

Gerald Lucovsky et al.
09/891,552
June 25, 2001
NOVEL NON-CRYSTALLINE OXIDES FOR USE IN MICROELECTRONIC,
OPTICAL, AND OTHER APPLICATIONS

December 3, 2002

Commissioner for Patents
Washington, DC 20231

TECHNOLOGY CENTER 2800
RECEIVED
DEC 11 2002

AMENDMENT

Sir:

This Amendment is responsive to the Office Action mailed September 5, 2002. It is respectfully requested that this application be reconsidered in view of amendments and remarks set forth below. Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The marked-up version of the changes is captioned "Version With Markings To Show Changes Made."

In the Specification:

Please replace the paragraph starting on page 1, line 3-6, with the following replacement paragraph:

-- Cross-Reference to Related Applications

B1
The present application claims priority to U.S. Provisional Application No. 60/214,285 filed June 26, 2000, the disclosure of which is incorporated herein by reference in its entirety.--

Please replace the paragraph starting on page 2, line 4-14, with the following replacement paragraph:

B2
-- Recently, aluminum oxide has been the focus of several studies. Klein *et al. Appl. Phys. Lett.* **75**, 4001 (1999) propose the deposition of aluminum oxide with a CVD growth method. This reference proposes a silicate layer being present at the interface on aluminum oxide and silicon, as measured by nuclear resonance profiling (NRP) and X-ray photoelectron spectroscopy (XPS). Gusev *et al. Appl. Phys. Lett.* **76**, 176 (2000) propose atomic layer CVD (ALCVD) where they investigated both the physical and electrical properties of an aluminum